

ABSTRACT

The present invention provides a final polishing method for a silicon single crystal wafer that performs final polishing with a polishing rate being set to 10 nm/min or below at a final polishing step as a final step among a plurality of polishing steps for polishing the silicon single crystal wafer with a polishing slurry being interposed between the silicon single crystal wafer and a polishing pad, and a silicon single crystal wafer subjected to final polishing by this method. Hereby, there can be provided the final polishing method that can obtain a silicon single crystal wafer with less PIDs (Polishing Induced Defects) and the silicon single crystal wafer subjected to final polishing by this method.